Yuzo Ohno

List of Publications by Year
in descending order

103	8,567	126858 33	42364 92
papers	citations	h-index	g-index

103	103	103	6964
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Spatiotemporal spin dynamics of two-dimensional electron gas with ballistic motion in persistent spin helix state. Physical Review B, 2022, 105, .	1.1	1
2	Room-temperature spinâ€“orbit magnetic fields in slightly misoriented (110) InGaAs/InAlAs multiple quantum wells. Applied Physics Letters, 2021, 119, 032405.	1.5	3
3	Impacts of Crystal Quality on Carrier Recombination and Spin Dynamics in (110)-Oriented GaAs/AlGaAs Multiple Quantum Wells at Room Temperature. Micromachines, 2021, 12, 1112.	1.4	1
4	Complex switching behavior of magnetostatically coupled single-domain nanomagnets probed by micro-Hall magnetometry. Applied Physics Letters, 2020, 116, .	1.5	4
5	Zero-field spin precession dynamics of high-mobility two-dimensional electron gas in persistent spin helix regime. Physical Review B, 2020, 101, .	1.1	4
6	Room-temperature spin relaxation in a (110)-oriented GaAs/AlGaAs superlattice with tunnel-coupled quantum wells. Applied Physics Express, 2020, 13, 123003.	1.1	3
7	Simultaneous extraction of Rashba and Dresselhaus spin-orbit coefficients in GaAs/AlGaAs (110) two-dimensional electron gas. , 2019, , .		0
8	Surface-mediated spin dynamics probed by optical-pumpâ€“probe scanning tunneling microscopy. Physical Chemistry Chemical Physics, 2019, 21, 7256-7260.	1.3	6
9	Evidence for Ferromagnetic Clusters in the Colossal-Magnetoresistance Material <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>EuB</mml:mi></mml:mrow><mml:mrow><mml:mn>6</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>. Physical Review Letters, 2018, 120, 257201.	2.9	33
10	Systematic study of surface morphology, photoluminescence efficiency, and spin-detection sensitivity in (110)-oriented GaAs/AlGaAs quantum wells. Japanese Journal of Applied Physics, 2016, 55, 113001.	0.8	3
11	Magnetic stray-field studies of a single Cobalt nanoelement as a component of the building blocks of artificial square spin ice. Journal of Magnetism and Magnetic Materials, 2016, 400, 206-212.	1.0	12
12	Vertical electric field induced suppression of fine structure splitting of excited state excitons in a single GaAs/AlGaAs island quantum dots. Applied Physics Letters, 2015, 107, 123102.	1.5	2
13	Nanocluster building blocks of artificial square spin ice: Stray-field studies of thermal dynamics. Journal of Applied Physics, 2015, 117, .	1.1	13
14	Growth condition dependence of photoluminescence polarization in (100) GaAs/AlGaAs quantum wells at room temperature. Journal of Applied Physics, 2015, 118, 083901.	1.1	2
15	Direct imaging of gate-controlled persistent spin helix state in a modulation-doped GaAs/AlGaAs quantum well. Applied Physics Express, 2014, 7, 013001.	1.1	47
16	Strain dependence of nuclear spin coherence in a (110)GaAs/AlGaAs quantum well. Japanese Journal of Applied Physics, 2014, 53, 093001.	0.8	2
17	Direct mapping of photoexcited local spins in a modulation-doped GaAs/AlGaAs wires. Japanese Journal of Applied Physics, 2014, 53, 04EM04.	0.8	6
18	Coherent Manipulation of Nuclear Spins in Semiconductors with an Electric Field. Applied Physics Express, 2013, 6, 033002.	1.1	15

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19	A strong anisotropy of spin dephasing time of quasi-one dimensional electron gas in modulation-doped GaAs/AlGaAs wires. Applied Physics Letters, 2013, 102, .	1.5	13
20	Detection and measurement of electroreflectance on quantum cascade laser device using Fourier transform infrared microscope. Applied Physics Letters, 2013, 103, 231106.	1.5	4
21	Photocurrent Measurements on a Quantum Cascade Laser Device by Fourier Transform Infrared Microscope. Japanese Journal of Applied Physics, 2012, 51, 06FE15.	0.8	2
22	Vertical-Electrical-Field-Induced Control of the Exciton Fine Structure Splitting in GaAs Island Quantum Dots for the Generation of Polarization-Entangled Photons. Japanese Journal of Applied Physics, 2012, 51, 06FE14.	0.8	1
23	Generation and control of polarization-entangled photons from GaAs island quantum dots by an electric field. Nature Communications, 2012, 3, 661.	5.8	76
24	Damage-free top-down processes for fabricating two-dimensional array of sub-10-nanometer GaAs nanodiscs using bio-template and neutral beam etching for intermediate band solar cell applications. , 2011, , .		0
25	Damage-free top-down processes for fabricating two-dimensional arrays of 7 nm GaAs nanodiscs using bio-templates and neutral beam etching. Nanotechnology, 2011, 22, 365301.	1.3	14
26	Magnetic Field Dependence of Quadrupolar Splitting and Nuclear Spin Coherence Time in a Strained (110) GaAs Quantum Well. Japanese Journal of Applied Physics, 2011, 50, 04DM03.	0.8	1
27	Width and temperature dependence of lithography-induced magnetic anisotropy in (Ga,Mn)As wires. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2685-2689.	1.3	2
28	Optical detection of zero-field spin precession of high mobility two-dimensional electron gas in a gated GaAs/AlGaAs quantum well. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2698-2701.	1.3	3
29	Detection of local electron and nuclear spin dynamics by time-resolved Kerr microscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2702-2706.	1.3	1
30	Observation of the fractional quantum Hall effect in an oxide. Nature Materials, 2010, 9, 889-893.	13.3	258
31	Defect-free etching process for GaAs/AlGaAs hetero-nanostructure using chlorine/argon mixed neutral beam. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 1138-1142.	0.6	17
32	Band-tail shape and transport near the metal-insulator transition in Si-doped<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mrow><mml:mn>0.3</mml:m Physical Review B, 2010, 82, .	1.1	8
33	Intersubband exchange interaction induced by optically excited electron spins in GaAs/AlGaAs quantum wells. Applied Physics Letters, 2009, 94, 162104.	1.5	2
34	Fabrication of a few-electron In0.56Ga0.44As vertical quantum dot with an Al2O3 gate insulator. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1930-1932.	1.3	0
35	0.7 anomaly and magnetotransport of disordered quantum wires. Europhysics Letters, 2008, 82, 27003.	0.7	4
36	Multipulse Operation and Optical Detection of Nuclear Spin Coherence in a<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>GaAs</mml:mi><mml:mo>/</mml:mo><mml:mi>AlGaAs</mml:mi></mml:math>Quantum Well. Physical Review Letters, 2008, 101, 207601.	2.9	28

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37	Low-temperature field-effect and magnetotransport properties in a ZnO based heterostructure with atomic-layer-deposited gate dielectric. Applied Physics Letters, 2008, 93, .	1.5	22
38	A few-electron vertical In0.56Ga0.44As quantum dot with an insulating gate. Applied Physics Letters, 2007, 91, 232101.	1.5	3
39	Magnetic Tunnel Junctions for Spintronic Memories and Beyond. IEEE Transactions on Electron Devices, 2007, 54, 991-1002.	1.6	460
40	Quantum Hall Effect in Polar Oxide Heterostructures. Science, 2007, 315, 1388-1391.	6.0	531
41	Effect of n+-GaAs thickness and doping density on spin injection of GaMnAs/n+-GaAs Esaki tunnel junction. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 438-441.	1.3	20
42	Decomposition of1/fNoise inAlxGa1â^'xAs/GaAsHall Devices. Physical Review Letters, 2006, 96, 186601.	2.9	29
43	Single-electron switching inAlxGa1â^'xAsâ^•GaAsHall devices. Physical Review B, 2006, 74, .	1.1	20
44	Low-frequency noise in submicron GaAs/AlxGa1â^'xAs Hall devices. Journal of Magnetism and Magnetic Materials, 2005, 290-291, 1161-1164.	1.0	1
45	Magnetization reversal in elongated Fe nanoparticles. Physical Review B, 2005, 71, .	1.1	17
46	Strong anisotropic spin dynamics in narrow n-InGaAsâ^•AlGaAs (110) quantum wells. Applied Physics Letters, 2005, 87, 171905.	1.5	21
47	Molecular Beam Epitaxy and Properties of Cr-Doped GaSb. Journal of Superconductivity and Novel Magnetism, 2004, 17, 349-352.	0.5	10
48	Electron spin dynamics in InGaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 1007-1011.	1.3	9
49	Modulation of Noise in SubmicronGaAs/AlGaAsHall Devices by Gating. Physical Review Letters, 2004, 93, 246602.	2.9	36
50	Zincblende CrSb/GaAs multilayer structures with room-temperature ferromagnetism. Materials Science in Semiconductor Processing, 2003, 6, 507-509.	1.9	24
51	Spin degree of freedom in ferromagnetic semiconductor heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 104-110.	1.3	6
52	Magnetization reversal of iron nanoparticles studied by submicron Hall magnetometry. Journal of Applied Physics, 2003, 93, 7912-7914.	1.1	7
53	High Mobility Thin Film Transistors with Transparent ZnO Channels. Japanese Journal of Applied Physics, 2003, 42, L347-L349.	0.8	267
54	Hall magnetometry on a single iron nanoparticle. Applied Physics Letters, 2002, 80, 4644-4646.	1.5	65

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55	Relaxation of photoinjected spins during drift transport in GaAs. Applied Physics Letters, 2002, 81, 2788-2790.	1.5	56
56	Anisotropic electrical spin injection in ferromagnetic semiconductor heterostructures. Applied Physics Letters, 2002, 80, 1598-1600.	1.5	53
57	Control of ferromagnetism in field-effect transistor of a magnetic semiconductor. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 351-355.	1.3	33
58	Valence band barrier at (Ga,Mn)As/GaAs interfaces. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 521-524.	1.3	33
59	Growth and properties of (Ga,Mn)As films with high Mn concentration. Journal of Applied Physics, 2001, 89, 7024-7026.	1.1	27
60	Spin-dependent phenomena in ferromagnetic/nonmagnetic IIIâ€“V heterostructures. Solid State Communications, 2001, 119, 281-289.	0.9	36
61	Spin-dependent properties of ferromagnetic/nonmagnetic GaAs heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 84, 70-74.	1.7	12
62	Spin relaxation in n-modulation doped GaAs/AlGaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 36-39.	1.3	51
63	Magnetotransport properties of (Ga,Mn)As grown on GaAs A substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 206-209.	1.3	27
64	Properties of (Ga,Mn)As/(Al,Ga)As/(Ga,Mn)As magnetic trilayer structures. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 278-282.	1.3	5
65	Temperature dependence of electroluminescence and Iâ€“V characteristics of ferromagnetic/non-magnetic semiconductor pn junctions. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 288-291.	1.3	16
66	Electrical spin injection in ferromagnetic/nonmagnetic semiconductor heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 489-492.	1.3	44
67	Effect of barrier width on the performance of quantum well infrared photodetector. Infrared Physics and Technology, 2001, 42, 115-121.	1.3	8
68	A Spin Esaki Diode. Japanese Journal of Applied Physics, 2001, 40, L1274-L1276.	0.8	125
69	Optical Manipulation of Nuclear Spin by a Two-Dimensional Electron Gas. Physical Review Letters, 2001, 86, 2677-2680.	2.9	142
70	Surfactant effect of Mn on the formation of self-organized InAs nanostructures. Journal of Crystal Growth, 2000, 208, 799-803.	0.7	18
71	Magnetotransport properties of (Ga,Mn)As investigated at low temperature and high magnetic field. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 976-980.	1.3	117
72	Molecular beam epitaxy of IIIâ€“V diluted magnetic semiconductor (Ga,Mn)Sb. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 981-985.	1.3	78

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73	Mobility dependence of electron spin relaxation time in n-type InGaAs/InAlAs multiple quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 1015-1019.	1.3	11
74	Bilayer Î½=2 quantum Hall state in parallel high magnetic field. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 615-618.	1.3	0
75	Electron spin relaxation beyond D'yakonovâ€“Perelâ€™ interaction in GaAs/AlGaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 817-820.	1.3	37
76	Surface morphologies of III-V based magnetic semiconductor (Ga,Mn)As grown by molecular beam epitaxy. Applied Surface Science, 2000, 166, 242-246.	3.1	5
77	Arsenic flux dependence of InAs nanostructure formation on GaAs (211)B surface. Applied Surface Science, 2000, 166, 413-417.	3.1	14
78	Electric-field control of ferromagnetism. Nature, 2000, 408, 944-946.	13.7	1,904
79	Magnetotransport studies of AlGaN/GaN heterostructures grown on sapphire substrates: Effective mass and scattering time. Applied Physics Letters, 2000, 76, 2737-2739.	1.5	42
80	Magnetoresistance effect and interlayer coupling of (Ga,â€ŠMn)As trilayer structures. Applied Physics Letters, 2000, 77, 1873.	1.5	143
81	Spin-dependent scattering in semiconducting ferromagnetic (Ga,Mn)As trilayer structures. Journal of Applied Physics, 2000, 87, 6436-6438.	1.1	22
82	Carrier Mobility Dependence of Electron Spin Relaxation in GaAs Quantum Wells. Japanese Journal of Applied Physics, 1999, 38, 2549-2551.	0.8	44
83	Electrical spin injection in a ferromagnetic semiconductor heterostructure. Nature, 1999, 402, 790-792.	13.7	2,315
84	MOCVD Growth and Transport Investigation of Two-Dimensional Electron Gas in AlGaN/GaN Heterostructures on Sapphire Substrates. Physica Status Solidi (B): Basic Research, 1999, 216, 743-748.	0.7	1
85	Electron mobility exceeding 104â€Šcm2/Vâ€Šs in an AlGaNâ€“GaN heterostructure grown on a sapphire substrate. Applied Physics Letters, 1999, 74, 3531-3533.	1.5	68
86	Spin Relaxation in GaAs(110) Quantum Wells. Physical Review Letters, 1999, 83, 4196-4199.	2.9	389
87	Î½=1 bilayer quantum Hall state at arbitrary electron distribution in a double quantum well. Solid-State Electronics, 1998, 42, 1183-1185.	0.8	0
88	Etched-backgate field-effect transistor structure for magnetotunneling study of low-dimensional electron systems. Solid-State Electronics, 1998, 42, 1187-1190.	0.8	0
89	Well-width dependence of bound to quasi-bound intersubband transition in GaAs quantum wells with multi-quantum barriers. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 200-203.	1.3	1
90	InAs quantum dots and dashes grown on (100), (211)B, and (311)B GaAs substrates. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 672-677.	1.3	18

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91	Spontaneous splitting of ferromagnetic (Ga, Mn)As valence band observed by resonant tunneling spectroscopy. Applied Physics Letters, 1998, 73, 363-365.	1.5	147
92	Interlayer exchange in (Ga,Mn)As/(Al,Ga)As/(Ga,Mn)As semiconducting ferromagnet/nonmagnet/ferromagnet trilayer structures. Applied Physics Letters, 1998, 73, 2122-2124.	1.5	53
93	Faraday rotation of ferromagnetic (Ga, Mn)As. Electronics Letters, 1998, 34, 190.	0.5	37
94	Phase Transition in thelî½=2Bilayer Quantum Hall State. Physical Review Letters, 1998, 80, 4534-4537.	2.9	104
95	Light emission spectra of AlGaAs/GaAs multiquantum wells induced by scanning tunneling microscope. Applied Physics Letters, 1998, 73, 1544-1546.	1.5	41
96	Photoluminescence Study of InAs Quantum Dots and Quantum Dashes Grown on GaAs(211)B. Japanese Journal of Applied Physics, 1998, 37, 1527-1531.	0.8	32
97	(Ga, Mn)As/GaAs Diluted Magnetic Semiconductor Superlattice Structures Prepared by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1997, 36, L73-L75.	0.8	48
98	Phototransistors Using Point Contact Structures. Japanese Journal of Applied Physics, 1997, 36, 1955-1957.	0.8	8
99	InAs self-organized quantum dashes grown on GaAs (211)B. Applied Physics Letters, 1997, 70, 2738-2740.	1.5	42
100	Anomalous stability of Î½ = 1 bilayer quantum Hall state. Solid State Communications, 1997, 103, 447-451.	0.9	12
101	Suppression of resonant tunneling in a coupled quantum well. Surface Science, 1996, 361-362, 142-145.	0.8	1
102	Photoluminescence from point contact structure â€" Direct observation of electron flow. Physica B: Condensed Matter, 1996, 227, 77-81.	1.3	2
103	Direct Observation of Electron Jet from a Point Contact. Japanese Journal of Applied Physics, 1996, 35, 1151-1153.	0.8	6